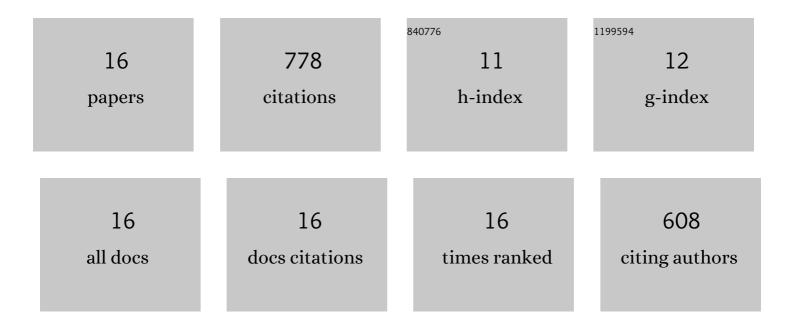
## James P Mcvittie

List of Publications by Year in descending order

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| #  | Article   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Ge-Interface Engineering With Ozone Oxidation for Low Interface-State Density. IEEE Electron Device<br>Letters, 2008, 29, 328-330.  | 3.9 | 172       |
| 2  | A tuned Langmuir probe for measurements in rf glow discharges. Journal of Applied Physics, 1990, 67,<br>6718-6727.  | 2.5 | 154       |
| 3  | Simulation of profile evolution in silicon reactive ion etching with re-emission and surface diffusion.<br>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B,<br>Microelectronics Processing and Phenomena, 1992, 10, 1091. | 1.6 | 133       |
| 4  | A twoâ€dimensional computer simulation for dry etching using Monte Carlo techniques. Journal of<br>Applied Physics, 1989, 65, 1484-1491.  | 2.5 | 73        |
| 5  | Charging damage to gate oxides in an O2magnetron plasma. Journal of Applied Physics, 1992, 72, 4865-4872.   | 2.5 | 69        |
| 6  | Core-Shell Germanium/Germanium–Tin Nanowires Exhibiting Room-Temperature Direct- and<br>Indirect-Gap Photoluminescence. Nano Letters, 2016, 16, 7521-7529.  | 9.1 | 54        |
| 7  | Model for oxide damage from gate charging during magnetron etching. Applied Physics Letters, 1993, 62, 1507-1509.   | 3.3 | 30        |
| 8  | lon trajectory distortion and profile tilt by surface charging in plasma etching. Applied Physics<br>Letters, 1994, 64, 1558-1560.  | 3.3 | 29        |
| 9  | Crystalâ€Orientation Dependent Etch Rates and a Trench Model for Dry Etching. Journal of the<br>Electrochemical Society, 1988, 135, 1521-1525.  | 2.9 | 27        |
| 10 | Integrating Phase-Change Memory Cell With Ge Nanowire Diode for Crosspoint Memory—Experimental<br>Demonstration and Analysis. IEEE Transactions on Electron Devices, 2008, 55, 2307-2313.   | 3.0 | 20        |
| 11 | Scaling laws for radio frequency glow discharges for dry etching. Journal of Vacuum Science and<br>Technology A: Vacuum, Surfaces and Films, 1990, 8, 1654-1662.  | 2.1 | 11        |
| 12 | In-Situ Monitoring of Electrical Parameters for Dry Etching. Materials Research Society Symposia<br>Proceedings, 1987, 98, 203.   | 0.1 | 4         |
| 13 | NEM relays using 2-dimensional nanomaterials for low energy contacts. , 2013, , .   |     | 2         |
| 14 | The Role of "Antenna―Structure on Thin Oxide Damage from Plasma Induced Wafer Charging.<br>Materials Research Society Symposia Proceedings, 1992, 265, 231.   | 0.1 | 0         |
| 15 | Limitations of Plasma Charging Damage Measurements Using MOS Capacitor Structures. Materials<br>Research Society Symposia Proceedings, 1996, 428, 349.  | 0.1 | 0         |
| 16 | Plasma induced wafer charging sensor. Journal of the Chinese Institute of Engineers, Transactions of<br>the Chinese Institute of Engineers,Series A/Chung-kuo Kung Ch'eng Hsuch K'an, 1998, 21, 11-19.  | 1.1 | 0         |